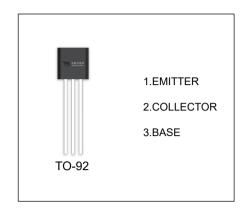


S9018 TRANSISTOR (NPN)

FEATURES

• High Current Gain Bandwidth Product



ORDERING INFORMATION

Part Number	umber Package Packing Method		Pack Quantity	
S9018	TO-92	Bulk	1000pcs/Bag	
S9018-TA	TO-92	Таре	2000pcs/Box	

MAXIMUM RATINGS (T_a =25 $^{\circ}$ C unless otherwise noted)

Symbol	Para meter Para meter	ter Value	
V _{CBO}	Collector-Base Voltage	25	
V _{CEO}	Collector-Emitter Voltage 18		V
V _{EBO}	Emitter-Base Voltage	4	V
Ic	Collector Current -Continuous	0.05	А
P _D	Collector Power Dissipation	400	mW
R _{0 JA}	Thermal Resistance from Junction to Ambient	312.5	°C /W
T_J , T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃



Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA,I _E =0	25			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =0.1mA,I _B =0	18			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA,I _C =0	4			V
Collector cut-off current	I _{CBO}	V _{CB} =20V,I _E =0			0.1	nA
Collector cut-off current	I _{CEO}	V _{CE} =15V,I _B =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =3V,I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =5V, I _C =1mA	28		270	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =10mA,I _B =1mA			0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =10mA,I _B =1mA			1.42	V
Transition frequency	f _T	V _{CE} =5V,I _C =50mA,f=400MHz		800		MHz

CLASSIFICATION OF h_{FE}

RANK	D	E	F	F G H		I	J
RANGE	28-45	39-60	54-80	72-108	97-146	132-198	180-270



